

Schottky Barrier Diodes

(Pb) Lead(Pb)-Free

Features:

- * Silicon Epitaxial Planar Diode
- * Low Reverse Current and Low Forward Voltage
- * Low Current Rectification and High Speed Switching
- * High Reliability
- * Used in Recorder, Radio, TV, Telephone as Detectors

Mechanical Data:

- * Case : MINI-MELF Glass Case (SOD-80)
- * Polarity: Color Band Denotes cathode Band
- * Weight : Approx 0.05 gram

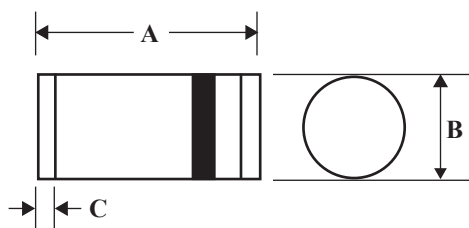
Schottky Barrier Diode
30-50 mAMPERES
40-45 VOLTS



MINI-MELF

MINI-MELF Outline Dimensions

Unit:mm



MINI MELF		
Dim	Min	Max
A	3.30	3.70
B	1.30	1.60
C	0.28	0.50

Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Characteristic	Symbol	LL60	LL60P	Unit
Peperitive Peak Reverse Voltage	V_{RRM}	40	45	V
Non-Repetitive Peak Forward Surge Current @ $t=1\text{S}$	I_{FSM}	150	500	mA
Forward Continuous Current, $T_A=25^{\circ}\text{C}$	I_F	30	50	mA
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +125		$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Characteristic	Symbol	Min	Tpy	Max	Unit
Forward Voltage $I_F=1\text{ mA}$ LL60 LL60P $I_F=30\text{ mA}$ LL60 $I_F=200\text{ mA}$ LL60P	V_F	- - - -	0.32 0.24 0.65 0.65	0.5 0.5 1.0 1.0	V
Rverse Current $V_R=15\text{V}$ LL60 LL60P	I_R	- -	0.1 0.5	0.5 1.0	μA
Junction Capacitance $V_R=1\text{V}, f=1\text{MHz}$ LL60 $V_R=10\text{V}, f=1\text{MHz}$ LL60P	C_j	- -	2.0 6.0	- -	PF
Reverse Recovery Time $I_F=I_R=1\text{mA}, I_{RR}=1\text{ mA}, R_C=100\ \Omega$	T_{rr}	-	-	1.0	nS

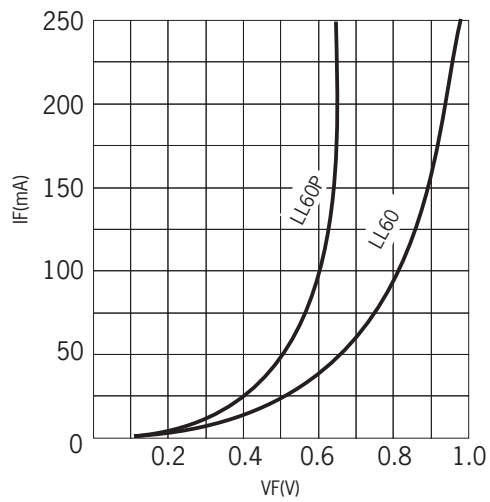


FIG.1 Forward Current vs. Forward Voltage

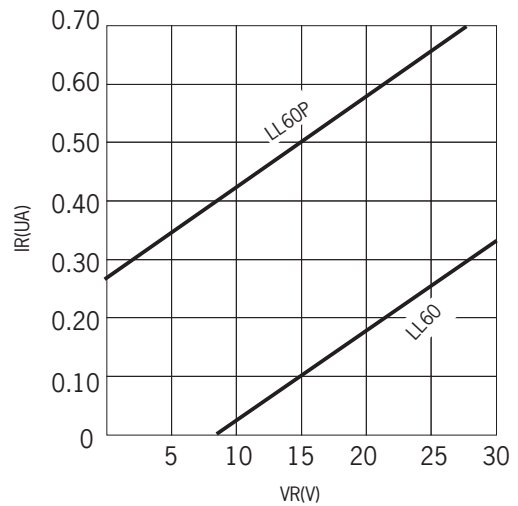


FIG.2 Reverse Current vs. Continuous Reverse Voltage

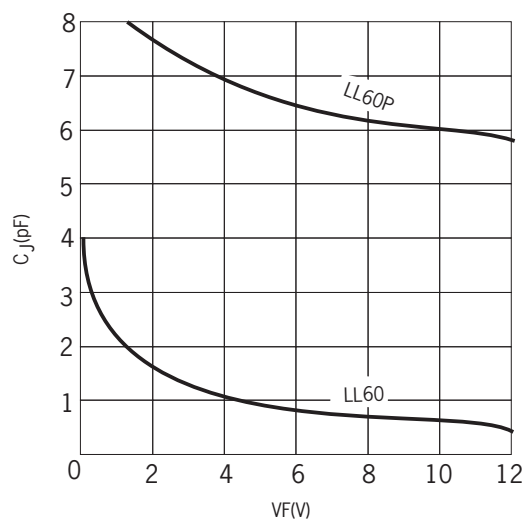


FIG.3 Junction Capacitance vs. Continuous Reverse Applied Voltage